

AMENDMENTS TO THE SPECIFICATION:

Please insert the following heading and paragraph on page 1, below the title:

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is a continuation of U.S. Patent Application No. 10/272,071, filed October 16, 2002, (pending), which is itself a divisional of U.S. Patent Application No. 09/656,631, filed September 7, 2000, now U.S. Patent No. 6,512,246, all of which are incorporated herein by reference.

Please amend the paragraph beginning on page 7, line 1, as follows:

In the structure according to ~~claims 2 and 3~~ various embodiments of the invention, either of at least one of the drain, channel and source regions or the cooling layer closely approaches the remainder.

Please amend the paragraph beginning on page 7, line 9, as follows:

In the structure according to ~~claim 4~~ another embodiment of the invention, a gate electrode is formed on the channel region, and the drain region closely approaches the cooling layer.

Please amend the paragraph beginning on page 7, line 20, as follows:

In the structure according to ~~claim 5~~ another embodiment of the invention, the cooling layer of the TFT has a shadowing property.

Please amend the paragraph beginning on page 8, line 11, as follows:

A method for fabricating a TFT according to ~~claim 7~~ one embodiment of the invention, comprises the steps of:

forming a semiconductor layer on a substrate,
forming a cooling layer with a higher heat conductivity than that of the semiconductor layer on the semiconductor layer,
patterning the cooling layer,
irradiating the semiconductor layer and the cooling layer with an energy beam, and
removing at least a portion of the cooling layer.

Please add the following paragraph beginning on page 10, below line 3:

FIGS. 7C and 7D show an outline of a structure of a TFT according to another embodiment of the invention, wherein FIG. 7C is a cross-sectional view for showing an outline of a structure of a TFT in an early stage of a fabrication process, and FIG. 7C shows a structure of a TFT in a later stage of a fabrication process.

Please amend the paragraph beginning on page 21, line 18, as follows:

Moreover, as shown in FIGS. 7C and 7D, as a modification of the aforementioned method for fabricating the TFT, another method that a cooling layer is formed and patterned on a semiconductor layer, the semiconductor layer and the cooling layer are irradiated with an energy beam and crystalline nucleuses are firstly formed in the semiconductor layer lying under the cooling layer can be devised.